



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the application of:

Kousuke SUZUKI, et al.

Serial Number: **09/045,118**

Group Art Unit: **2823**

Filed: **March 20, 1998**

Examiner: **N. Berezny**

For: **SEMICONDUCTOR DEVICE HAVING AN INSULATION FILM WITH REDUCED
WATER CONTENT (AS AMENDED)**

PRELIMINARY AMENDMENT

Director of Patents and Trademarks
Washington, D.C. 20231

April 15, 2002

Sir:

Prior to continued prosecution, please amend the application as follows:

IN THE SPECIFICATION:

Please replace the paragraph beginning at page 15, line 24, with the following, rewritten paragraph:

E1
--Referring to FIGS. 3 and 4, it can be seen that a substantial release of H_2O and OH occurs in the SiO_2 film deposited under a conventional plasma power of 200W immediately after the start of the heating. The release of H_2O and OH continues even when the temperature reaches 1000°C.--